

Device Modeling Report

COMPONENTS:
DIODE/ ENHANCED POWER LED / STANDARD
PART NUMBER: EP204K-35G1R1B1-CA
MANUFACTURER: PARA Light
EMARK: 25 degree C
COLER: RED

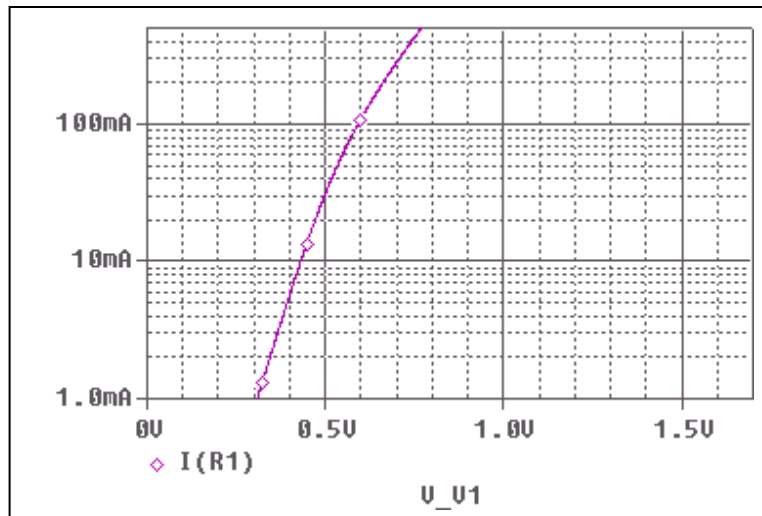


Bee Technologies Inc.

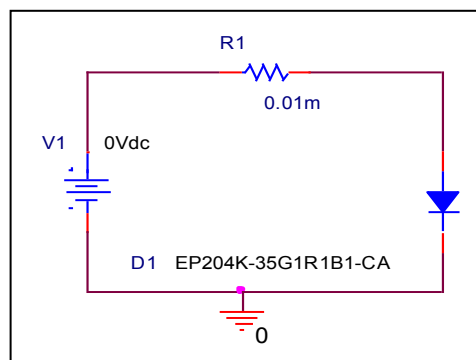
PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

Forward Current Characteristic

Circuit Simulation Result

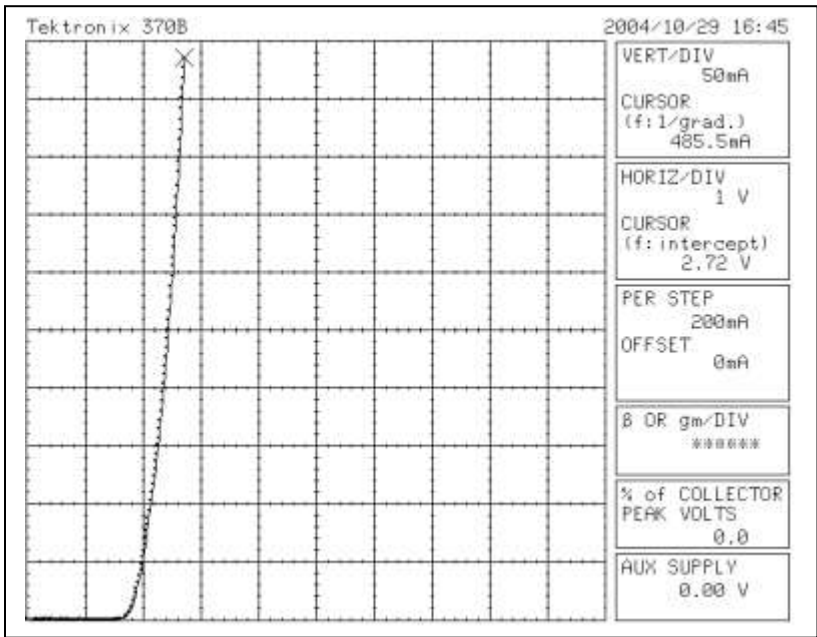


Evaluation Circuit



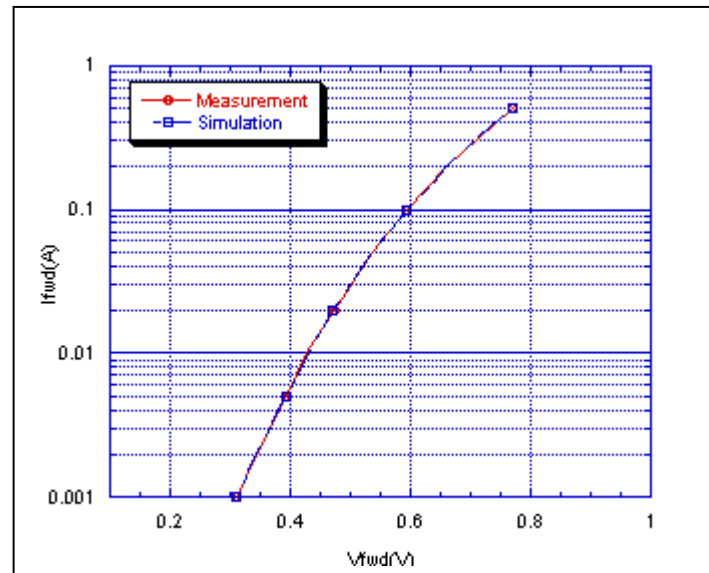
Forward Current Characteristic

Reference



Comparison Graph

Circuit Simulation Result

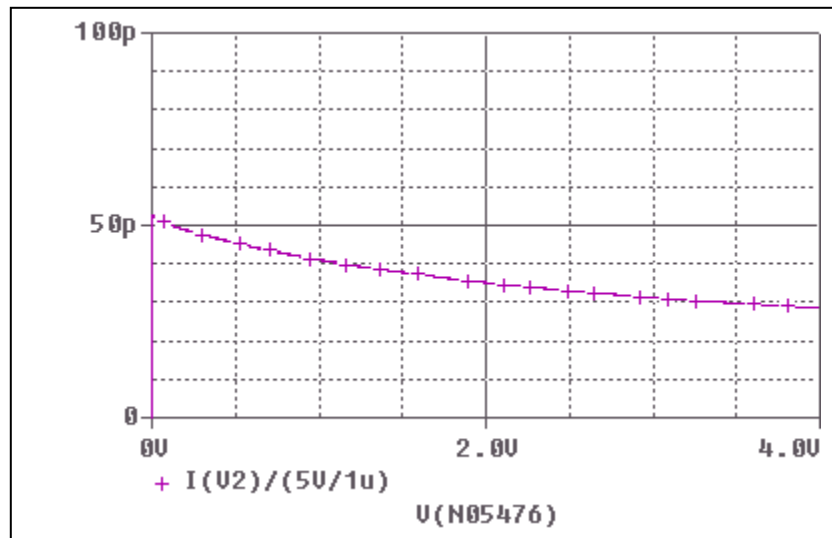


Simulation Result

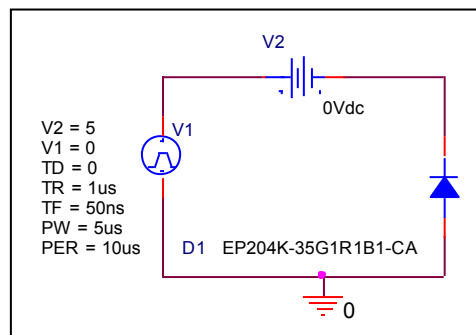
$I_{fwd}(A)$	$V_{fwd}(V)$ Measurement	$V_{fwd}(V)$ Simulation	%Error
0.001	0.311	0.3088	0.7073
0.002	0.343	0.3444	0.4081
0.005	0.392	0.3928	0.2040
0.01	0.428	0.431	0.7009
0.02	0.473	0.4713	0.3594
0.05	0.537	0.5352	0.3351
0.1	0.593	0.5924	0.1011
0.2	0.659	0.6618	0.4248
0.5	0.771	0.771	0

Capacitance Characteristic

Circuit Simulation Result

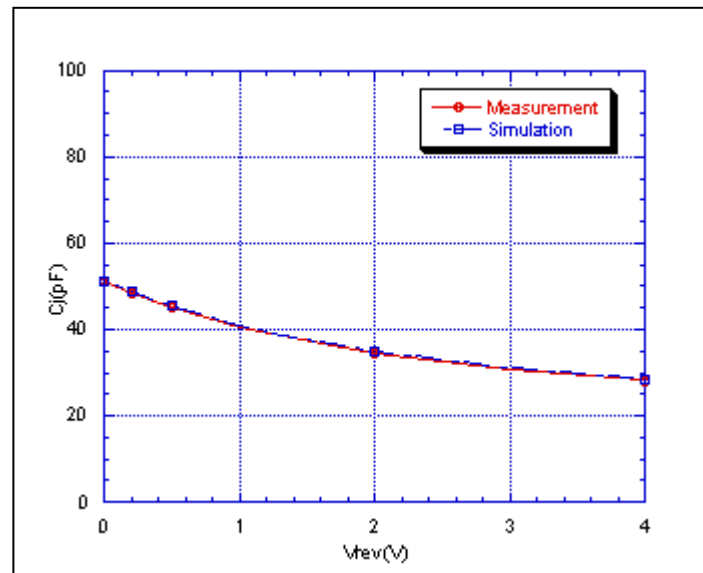


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

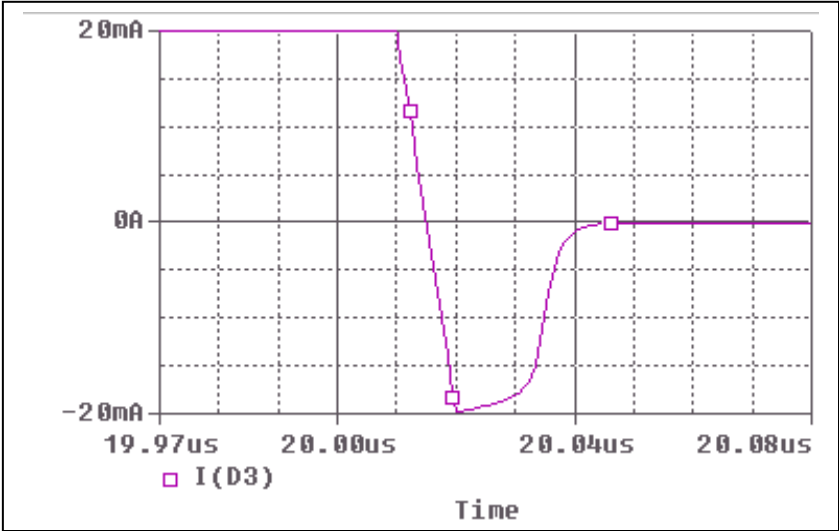


Simulation Result

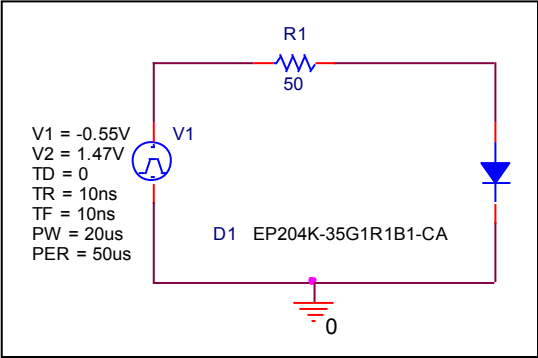
V_{rev} (V)	C_j (pF) Measurement	C_j (pF) Simulation	%Error
0	51.038	51.038	0
0.1	49.705	50.252	1.100
0.2	48.48	48.839	0.740
0.5	44.98	45.44	1.022
1	40.59	40.817	0.559
2	34.59	35.031	1.274
3	30.74	31.061	1.044
4	28.09	28.443	1.256

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

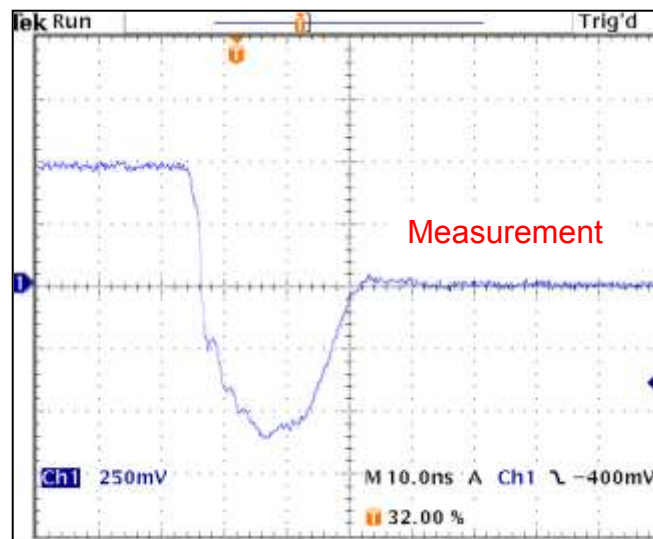


Compare Measurement vs. Simulation

Symbol	Measurement	Unit	Simulation	Unit	%Error
Trr=trj+trb	23	ns	23	ns	0

Reverse Recovery Characteristic

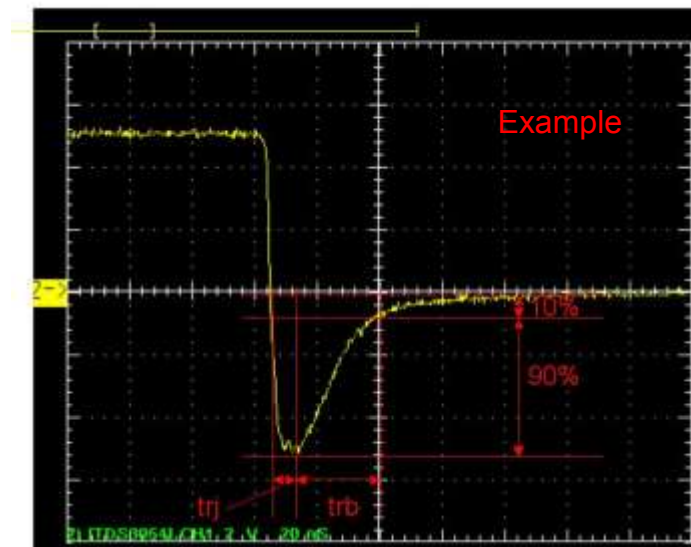
Reference



$T_{rj} = 10.2(\text{ns})$

$T_{rb} = 12.8(\text{ns})$

Conditions: $I_{fwd} = I_{rev} = 0.2(\text{A})$, $R_I = 50$



Relation between t_{rj} and t_{rb}